Description

The DLSR05 is a low capacitance TVS diode array, utilizing leading monolithic silicon technology to provide fast response time and low ESD clamping voltage, making this device an ideal solution for protecting sensitive semiconductor components from damage. The DLSR05 complies with the IEC 61000-4-2(ESD) standard with ±30kV air and ±30kV contact discharge. It is assembled into a lead-free SOT-143 package. It is designed to protect components which are connected to high speed interfaces and transmission lines from voltage surges.

Features

- 600W peak pulse power(8/20μs)
- Ultra low leakage：nA level
- Operating voltage：5V
- Low capacitance for high-speed data line
- Low clamping voltage
- Complies with following standards:
  - IEC 61000-4-2 (ESD) immunity test
    Air discharge: ±30kV
    Contact discharge: ±30kV
  - IEC61000-4-4 (EFT) 40A (5/50ns)
  - IEC61000-4-5 (Lightning) 30A (8/20μs)
- RoHS Compliant

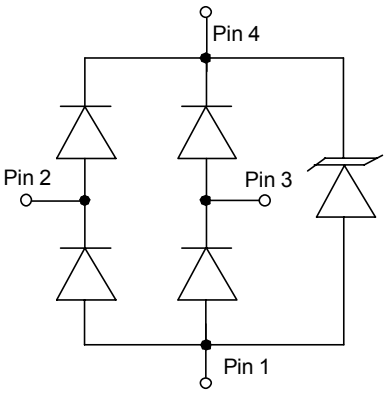
Mechanical Characteristics

- Package: SOT-143
- Lead Finish: Matte Tin
- Case Material: “Green” Molding Compound.
- UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 3 per J-STD-020
- Terminal Connections: See Diagram Below
- Marking Information: See Below

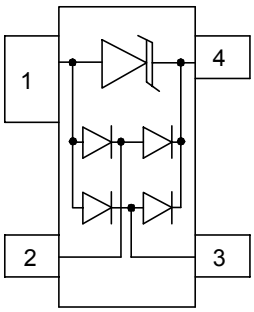
Applications

- Video Line Protection
- Wireless Systems
- Ethernet 10BaseT
- I2C Bus Protection
- Portable Instrumentation
- LAN/WAN equipment
- High-Speed Data Lines
- Multi-Protocol Serial Transceivers
- ISDN S/T Interface

Dimensions and Pin Configuration

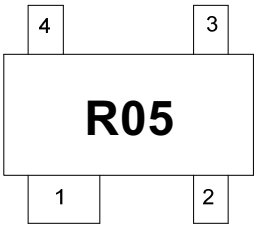


Circuit Diagram



Pin Schematic

Marking Information



Ordering Information

Part Number	Marking	Packaging	Reel Size
DLSR05	R05	3000/Tape & Reel	7 inch

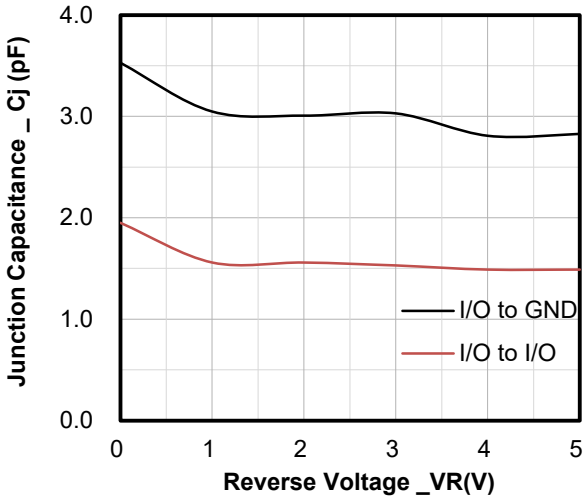
Absolute Maximum Ratings (T_A=25°C unless otherwise specified)

Parameter	Symbol	Value	Unit
Peak Pulse Power(8/20μs)	Ppk	600	W
Peak Pulse Current(8/20μs)	I_{PP}	30	A
ESD per IEC 61000−4−2 (Air) ESD per IEC 61000−4−2 (Contact)	V_{ESD}	±30 ±30	kV
Operating Temperature Range	T_J	−55 to +125	°C
Storage Temperature Range	Tstg	−55 to +150	°C

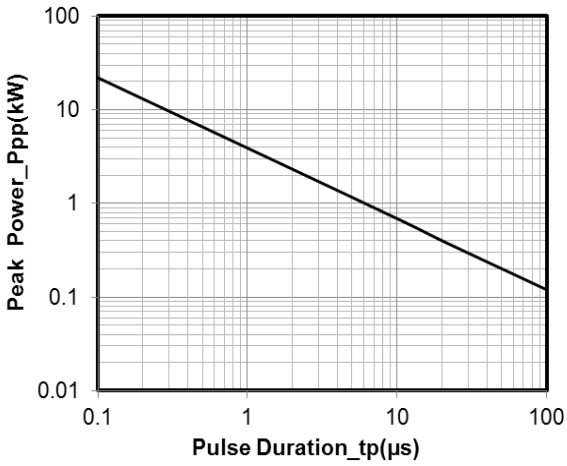
Electrical Characteristics (T_A=25°C unless otherwise specified)

Parameter	Symbol	Min	Typ	Max	Unit	Test Condition
Reverse Working Voltage	V_{RWM}			5	V	
Punch-Through Voltage	V_{BR}	6			V	I_T = 1mA
Reverse Leakage Current	I_R			0.5	μA	V_{RWM} = 5V
Clamping Voltage	V_C			10	V	I_{PP} = 1A (8 x 20μs pulse), between I/O pins and GND
Clamping Voltage	V_C			13	V	I_{PP} = 15A (8 x 20μs pulse), between I/O pins and GND
Clamping Voltage	V_C			18	V	I_{PP} = 30A (8 x 20μs pulse), between I/O pins and GND
Junction Capacitance	C_J			4.0	pF	VR=0, f=1MHz, between I/O pins and GND
Junction Capacitance	C_J			2.0	pF	VR=0, f=1MHz, between I/O pins

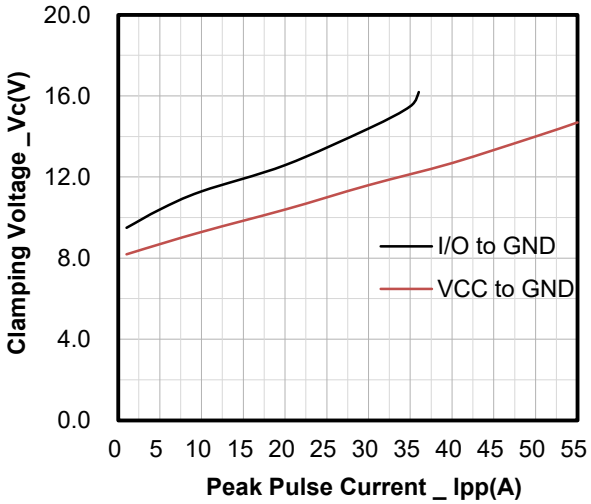
Typical Performance Characteristics (T_A=25℃ unless otherwise Specified)



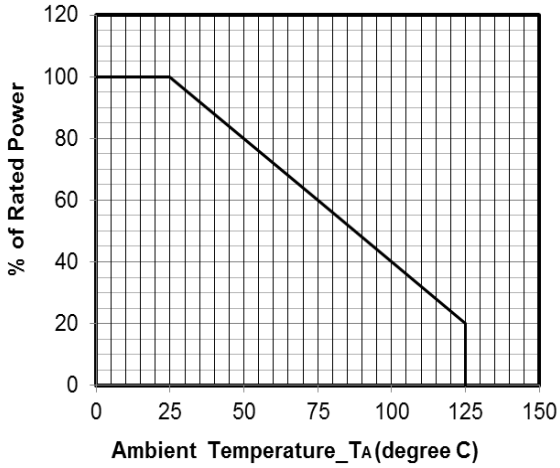
Junction Capacitance vs. Reverse Voltage



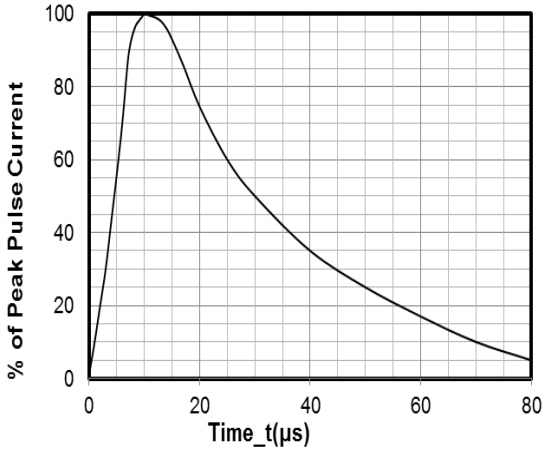
Peak Pulse Power vs. Pulse Time



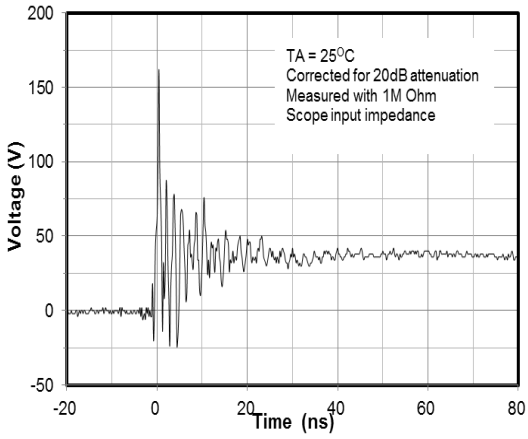
Clamping Voltage vs. Peak Pulse Current



Power Derating Curve



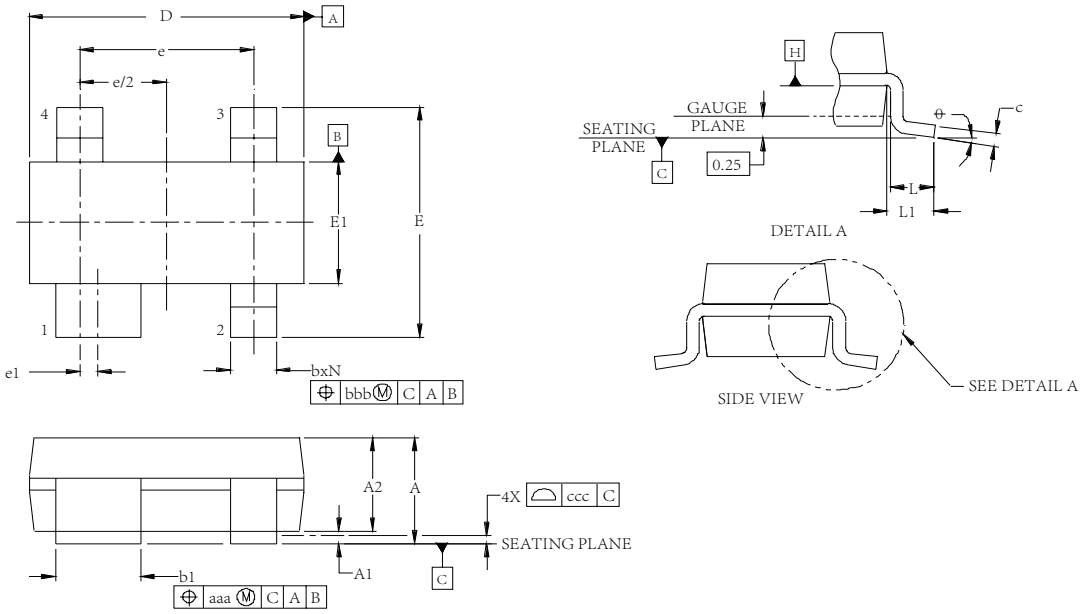
8 X 20μs Pulse Waveform



ESD Clamping Voltage

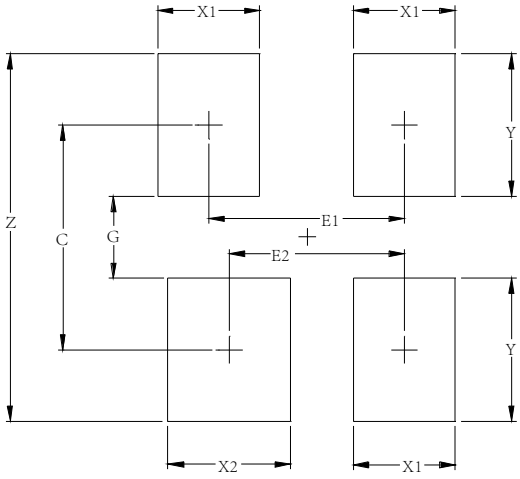
8 kV Contact per IEC61000−4−2

SOT-143 Package Outline Drawing



DIM	INCHES			MILLIMETERS		
	MIN	NOM	MAX	MIN	NOM	MAX
A	.031	-	.048	0.80	-	1.22
A1	.000	-	.006	0.013	-	0.15
A2	.029	.035	.042	0.75	0.90	1.07
b	.011	-	.020	0.30	-	0.51
b1	.029	-	.037	0.76	-	0.94
c	.003	-	.008	0.08	-	0.20
D	.110	.114	.120	2.80	2.90	3.04
E	.082	.093	.104	2.10	2.37	2.64
E1	.047	.051	.055	1.20	1.30	1.40
e	.075			1.92 BSC		
e1	.008			0.20 BSC		
L	.015	.020	.024	0.40	0.50	0.60
L1	(.021)			(0.54)		
N	4			4		
θ	0°	-	8°	0°	-	8°
aaa	.006			0.15		
bbb	.008			0.20		
ccc	.004			0.10		

Suggested Land Pattern



SYM	DIMENSIONS	
	MILLIMETERS	INCHES
C	2.20	0.087
E1	1.92	0.076
E2	1.72	0.068
G	0.80	0.031
X1	1.00	0.039
X2	1.20	0.047
Y	1.40	0.055
Z	3.60	0.141

Contact Information

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